

HIGH-TEMPERATURE, 80V N-CHANNEL POWER MOSFET FAMILY

FEATURES

- ▲ Minimum $BV_{DSS} = 100V$.
- ▲ Allowed V_{GS} range $-5.5V$ to $+5.5V$.
- ▲ Operational beyond the $-60^{\circ}C$ to $+230^{\circ}C$ temperature range.
- ▲ Low $R_{DS(on)}$
 - XTR2N0825: $1.8 \Omega @ 230^{\circ}C$
 - XTR2N0850: $0.79 \Omega @ 230^{\circ}C$
- ▲ Maximum I_D :
 - XTR2N0825: $5A @ 230^{\circ}C$
 - XTR2N0850: $11.5A @ 230^{\circ}C$
- ▲ On-time ($t_{d(on)}+t_r$):
 - XTR2N0825: $80nsec @ 230^{\circ}C$
 - XTR2N0850: $95nsec @ 230^{\circ}C$
- ▲ Off-time ($t_{d(off)}+t_f$):
 - XTR2N0825: $75nsec @ 230^{\circ}C$
 - XTR2N0850: $75nsec @ 230^{\circ}C$
- ▲ Ruggedized 3-lead TO257 and SMD packages.
- ▲ Also available as bare die.

DESCRIPTION

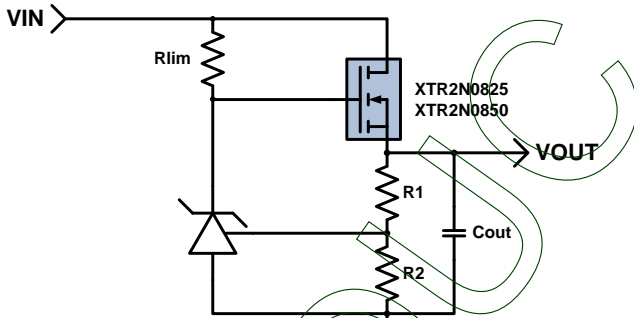
XTR2N0800 is a family of N-channel power MOSFETs designed to reliably operate over a wide range of temperatures. Full functionality is guaranteed from $-60^{\circ}C$ to $+230^{\circ}C$, though operation well below and above this temperature range is achieved. Fabricated on a Silicon-on-Insulator (SOI) process, XTR2N0800 family parts offer reduced leakage currents while providing high drain currents and low $R_{DS(on)}$. These features allow XTR2N0800 parts to be ideally suited for switching applications. XTR2N0800 family parts have been designed to reduce system cost and ease adoption by reducing the learning curve and providing smart and easy to use features. Parts from the XTR2N0800 family are available in ruggedized 3-lead TO257 and SMD power packages. Parts are also available as bare dies.

APPLICATIONS

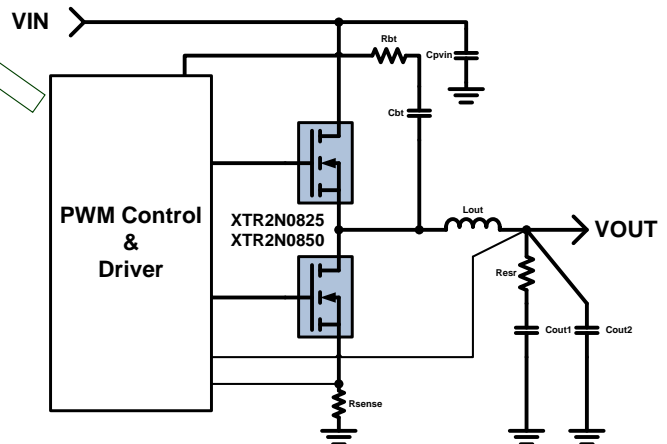
- ▲ Reliability-critical, Automotive, Aeronautics & Aerospace, Down-hole.
- ▲ DC/DC converters, power switching, motor control, power inverters, power linear regulators, power supply.

PRODUCT HIGHLIGHT

Power Series Regulator



Step-down DC-DC Converter



ORDERING INFORMATION

X
↓
Source:
X = X-REL Semi

TR
↓
Process:
TR = HiTemp, HiRel
R = HiRel

2N
↓
Part family

08xx
↓
Part number

Product Reference	Temperature Range	Package	Pin Count	Marking
XTR2N0825-BD	$-60^{\circ}C$ to $+230^{\circ}C$	Bare die		XTR2N0825
XTR2N0850-BD	$-60^{\circ}C$ to $+230^{\circ}C$	Bare die		XTR2N0850
XTR2N0825-D	$-60^{\circ}C$ to $+230^{\circ}C$	Ceramic side Braze DIP	8	XTR2N0825
XTR2N0825-Y	$-60^{\circ}C$ to $+230^{\circ}C$	TO-257AA	3	XTR2N0825
XTR2N0850-T	$-60^{\circ}C$ to $+230^{\circ}C$	TO-257AA	3	XTR2N0850
XTR2N0825-M	$-60^{\circ}C$ to $+230^{\circ}C$	SMD-0.5	3	XTR2N0825
XTR2N0850-M	$-60^{\circ}C$ to $+230^{\circ}C$	SMD-1	3	XTR2N0850

Other packages and packaging configurations possible upon request.

ABSOLUTE MAXIMUM RATINGS

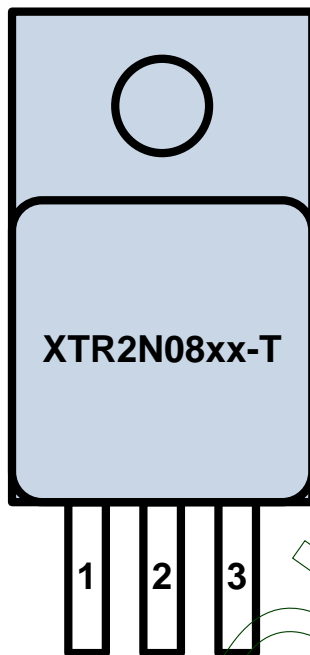
Drain-source voltage	-2V to +100V
Gate-source voltage	±6.0V
Storage temperature range	-70°C to +230°C
Operating junction temperature range	-70°C to +300°C
ESD classification	1kV HBM MIL-STD-883

Caution: Stresses beyond those listed in “ABSOLUTE MAXIMUM RATINGS” may cause permanent damage to the device. These are stress ratings only and functionality of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to “ABSOLUTE MAXIMUM RATINGS” conditions for extended periods may permanently affect device reliability.

PRODUCT VARIANTS

TO-257

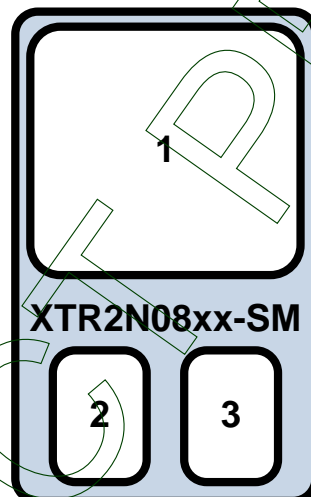
Front view



- 1 DRAIN
- 2 SOURCE
- 3 GATE

SMD-0.5 / SMD-1

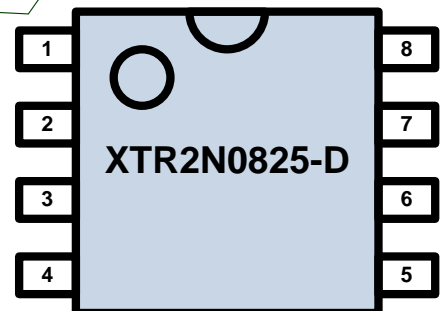
Bottom view



- 1 SOURCE
- 2 GATE
- 3 DRAIN

DIP8

Top view



- 1, 2, 3 SOURCE
- 4 GATE
- 5, 6, 7, 8 DRAIN

RECOMMENDED OPERATING CONDITIONS

Parameter	Min	Typ	Max	Units
Drain-source voltage V_{DS}	-1.5		80	V
Gate-source voltage V_{GS}	-5.5		+5.5	V
Junction Temperature ¹ T_j	-60		230	°C

¹ Operation beyond the specified temperature range is achieved.

XTR2N0825 SPECIFICATIONS

Unless otherwise stated, specification applies for $-60^{\circ}\text{C} < T_j < 230^{\circ}\text{C}$.

Parameter	Condition	Min	Typ	Max	Units
DC Characteristics					
Drain-source breakdown voltage BV_{DSS}	$V_{GS}=0V, I_{DS}=100\mu A, T_j=25^{\circ}\text{C}$	100			V
Static drain-source on-state resistance $R_{DS(on)}$	$V_{GS}=+5V, I_{DS}=100mA$ $T_j=-60^{\circ}\text{C}$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		0.65 0.75 1.50		Ω
Gate threshold voltage $V_{GS(th)}$	$V_{DS}=V_{GS}, T_j=25^{\circ}\text{C}, I_{DS}=100\mu A$	1.4	1.6	1.8	V
Temperature drift of gate threshold voltage $\Delta V_{GS(th)}/\Delta T_j$	$V_{DS}=V_{GS}, I_{DS}=100\mu A$		-3.5		mV/°C
Off-state drain current I_{DSS}	$V_{DS}=80V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		0.0009 12		μA
Off-state gate current I_{GSS}	$V_{GS}=\pm 5V, V_{DS}=0V$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		± 0.2 ± 80		nA
AC Characteristics					
Input capacitance C_{iss}	$V_{DS}=80V, V_{GS}=0V, f=1MHz$		310		pF
Output capacitance C_{oss}			75		pF
Reverse transfer capacitance C_{rss}			30		pF
Switching Characteristics					
Pulsed drain current I_{DM}	$V_{DS}=80V, V_{GS\ sweep}=0\ to\ +5V, d=0.2\%, \tau=1ms$ $T_j=-60^{\circ}\text{C}$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		5 4 2.5		A
Total gate charge Q_g	$V_{DS}=80V, V_{GS\ sweep}=0\ to\ +5V$		3		nC
Turn-on delay time $t_{d(on)}$	$V_{DS}=20V, V_{GS\ sweep}=0\ to\ +5V, d=0.2\%, \tau=1ms$		30		ns
Rise time t_r	$V_{DS}=20V, V_{GS\ sweep}=0\ to\ +5V, d=0.2\%, \tau=1ms$		50		
Turn-off delay time $t_{d(off)}$	$V_{DS}=20V, V_{GS\ sweep}=+5\ to\ 0V, d=0.2\%, \tau=1ms$		50		
Fall time t_f	$V_{DS}=20V, V_{GS\ sweep}=+5\ to\ 0V, d=0.2\%, \tau=1ms$		25		
Thermal Characteristics					
Junction-case thermal resistance θ_{j-c}	TO-257 SMD-0.5		TBD		°C/W
Junction-ambient thermal resistance θ_{j-a}	TO-257 SMD-0.5		TBD		°C/W

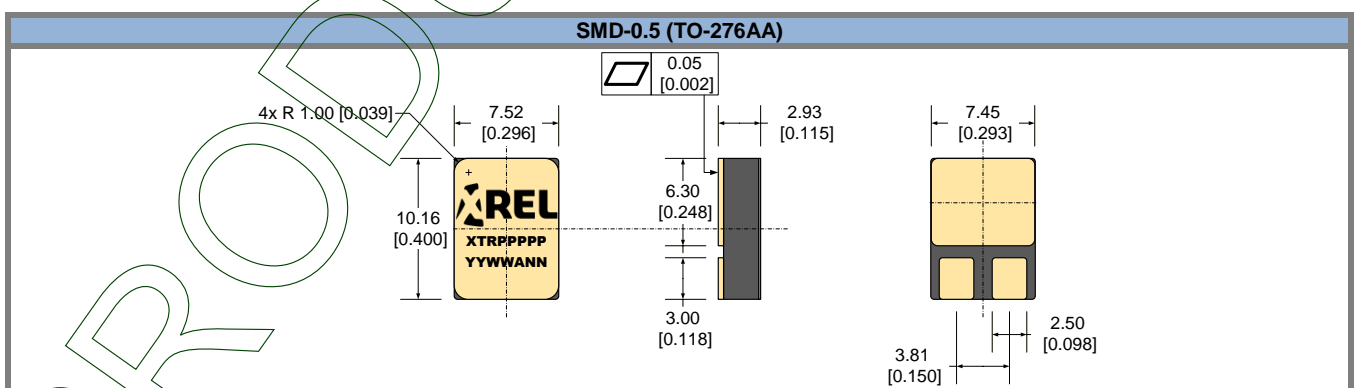
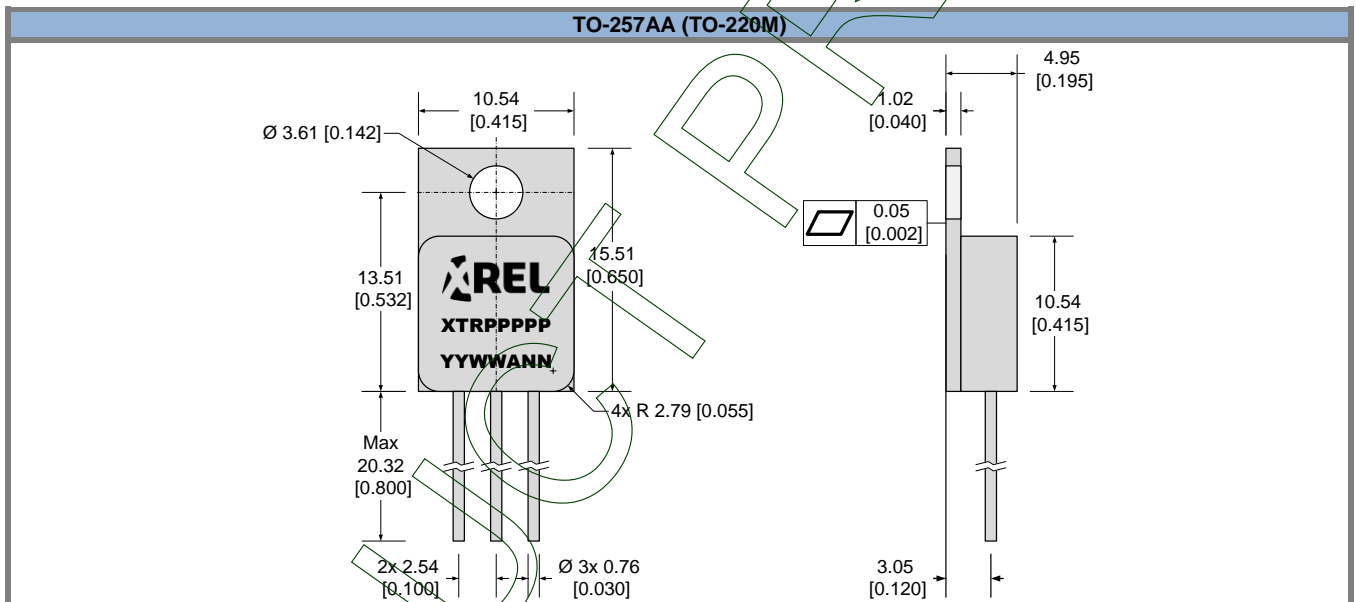
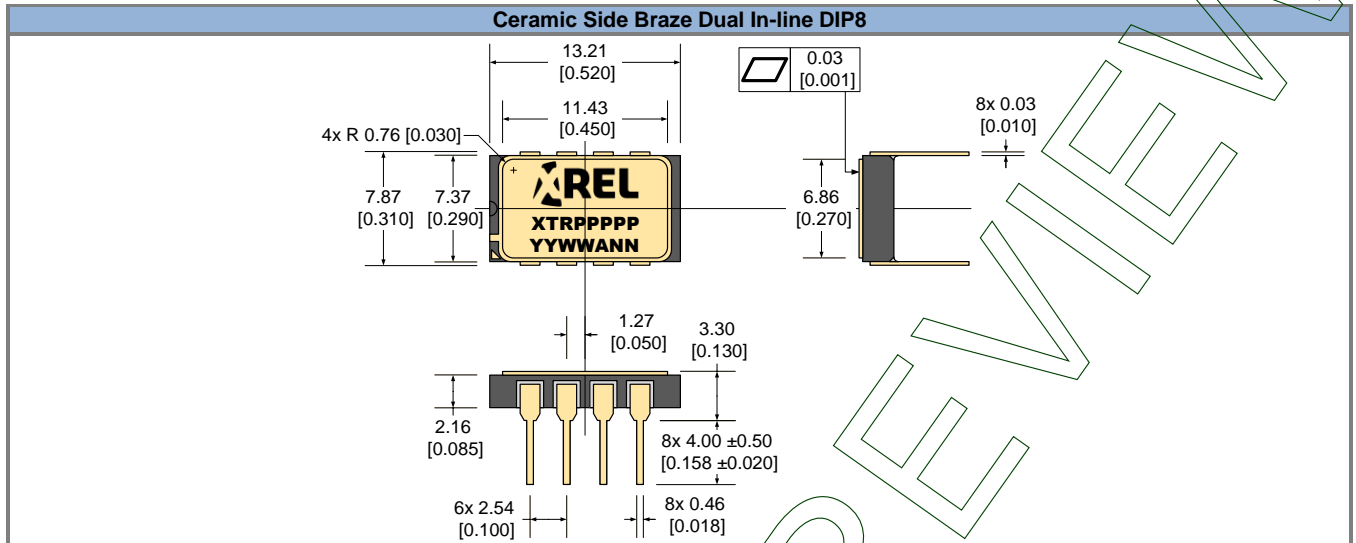
XTR2N0850 SPECIFICATIONS

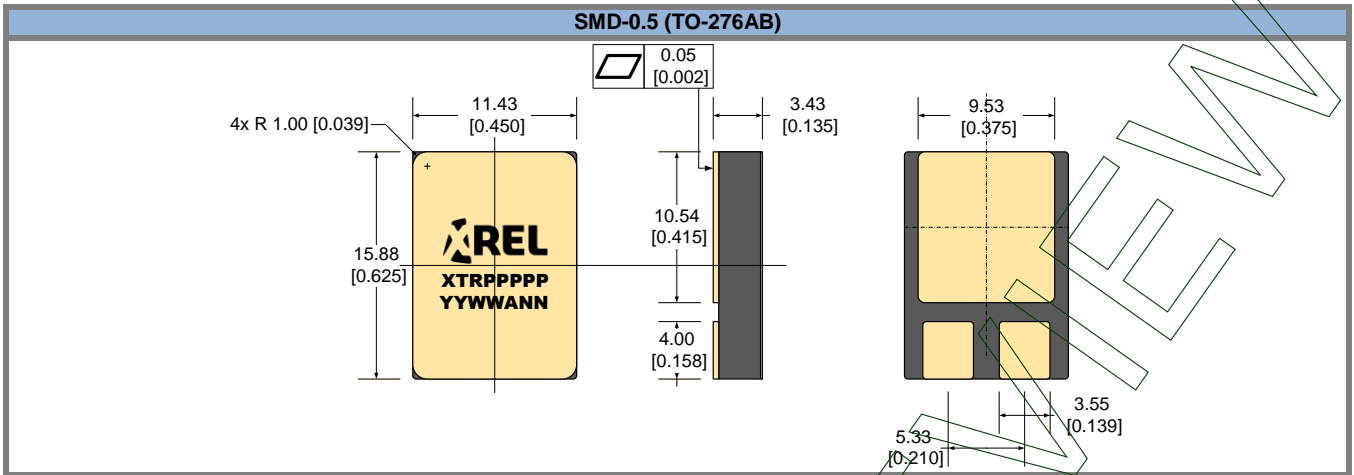
 Unless otherwise stated, specification applies for $-60^{\circ}\text{C} < T_j < 230^{\circ}\text{C}$.

Parameter	Condition	Min	Typ	Max	Units
DC Characteristics					
Drain-source breakdown voltage BV_{DSS}	$V_{GS}=0V, I_{DS}=100\mu A$	100			V
Static drain-source on-state resistance $R_{DS(on)}$	$V_{GS}=+5V, I_{DS}=100mA$ $T_j=-60^{\circ}\text{C}$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		0.33 0.40 0.79		Ω
Gate threshold voltage $V_{GS(th)}$	$V_{DS}=V_{GS}, T_j=25^{\circ}\text{C}, I_{DS}=100\mu A$	1.4	1.6	1.8	V
Temperature drift of gate threshold voltage $\Delta V_{GS(th)}/\Delta T_j$	$V_{DS}=V_{GS}, I_{DS}=100\mu A$		-3.5		mV/ $^{\circ}\text{C}$
Off-state drain current I_{DSS}	$V_{DS}=80V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		0.0025 29		μA
Off-state drain current I_{GSS}	$V_{GS}=\pm 5V, V_{DS}=0V$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		± 0.2 ± 80		nA
AC Characteristics					
Input capacitance C_{iss}	$V_{DS}=80V, V_{GS}=0V, f=1\text{MHz}$		750		pF
Output capacitance C_{oss}			180		pF
Reverse transfer capacitance C_{rss}			75		pF
Switching Characteristics					
Pulsed drain current I_{DM}	$V_{DS}=80V, V_{GS \text{ sweep}}=0 \text{ to } +5V, d=0.2\%, \tau=1\text{ms}$ $T_j=-60^{\circ}\text{C}$ $T_j=25^{\circ}\text{C}$ $T_j=230^{\circ}\text{C}$		11.5 9.5 5.8		A
Total gate charge Q_g	$V_{DS}=80V, V_{GS \text{ sweep}}=0 \text{ to } +5V$		7		nC
Turn-on delay time $t_{d(on)}$	$V_{DS}=20V, V_{GS \text{ sweep}}=0 \text{ to } +5V, d=0.2\%, \tau=1\text{ms}$		40		ns
Rise time t_r	$V_{DS}=20V, V_{GS \text{ sweep}}=0 \text{ to } +5V, d=0.2\%, \tau=1\text{ms}$		55		
Turn-off delay time $t_{d(off)}$	$V_{DS}=20V, V_{GS \text{ sweep}}=+5 \text{ to } 0V, d=0.2\%, \tau=1\text{ms}$		55		
Fall time t_f	$V_{DS}=20V, V_{GS \text{ sweep}}=+5 \text{ to } 0V, d=0.2\%, \tau=1\text{ms}$		30		
Thermal Characteristics					
Junction-case thermal resistance θ_{j-c}	TO-257 SMD-1		TBD		$^{\circ}\text{C/W}$
Junction-ambient thermal resistance θ_{j-a}	TO-257 SMD-1		TBD		$^{\circ}\text{C/W}$

PACKAGE OUTLINES

Dimensions shown in mm [inches].





Part Marking Convention	
Part Reference: XTRPPPPPP	
XTR	X-REL Semiconductor, high-temperature, high-reliability product (XTRM Series).
PPPPP	Part number (0-9, A-Z).
Unique Lot Assembly Code: YYWWANN	
YY	Two last digits of assembly year (e.g. 11 = 2011).
WW	Assembly week (01 to 52).
A	Assembly location code.
NN	Assembly lot code (01 to 99).

PRODUCT RELEASE

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